

Serial No. 09/611,955  
Art Unit: 2811

**IN THE CLAIMS**

Kindly amend claims 25, 31 and 32 to appear as follows:

D4  
25. (Thrice Amended) A semiconductor structure, comprising: a semiconductor substrate; a recess located in at least one major surface of said semiconductor substrate; an electrical insulating layer located over said at least one major surface and in said recess; a conductive barrier located over said insulating layer in said recess and over said at least one major surface; a plating seed layer located over said conductive barrier within said recess only, and a conductive metal in said recess only.

D5  
31. (Amended) The semiconductor structure of claim 25 wherein said conductive metal is copper.

32. (Amended) The semiconductor structure of claim 31 wherein said conductive metal is about 4000 Å to about 30,000 Å thick.

**REMARKS**

Applicant amended claim 25, for further clarity, and claims 31 and 32 per the Examiner's suggestion. Applicant amended the specification at pages 7 and 13 to recite "in", as supported, e.g., in originally filed claims 1, 25.